

Data Sheet January 2000 File Number 3388.3

80A, 600V Ultrafast Diode

The RURG8060 is an ultrafast diode with soft recovery characteristics (t_{rr} < 75ns). It has low forward voltage drop and is of silicon nitride passivated ion-implanted epitaxial planar construction.

This device is intended for use as a freewheeling/clamping diode and rectifier in a variety of switching power supplies and other power switching applications. Its low stored charge and ultrafast recovery with soft recovery characteristic minimize ringing and electrical noise in many power switching circuits, thus reducing power loss in the switching transistors.

Formerly developmental type TA09886.

Ordering Information

PART NUMBER	PACKAGE	BRAND		
RURG8060	TO-247	RURG8060		

NOTE: When ordering, use the entire part number.

Symbol



勝 特 力 材 料 886-3-5753170 胜特力电子(上海) 86-21-54151736 胜特力电子(深圳) 86-755-83298787 Http://www.100y.com.tw

Features

•	Ultrafast with Soft Recovery	<75ns
	Operating Temperature	175 ⁰ C
•	Reverse Voltage	600V

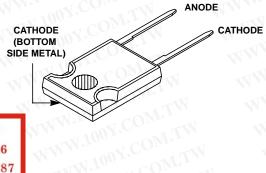
- Avalanche Energy Rated
- Planar Construction

Applications

- Switching Power Supplies
- · Power Switching Circuits
- General Purpose

Packaging

JEDEC STYLE 2 LEAD TO-247



Absolute Maximum Ratings T _C = 25°C, Unless Otherwise Specified	100 L COM. 1	
	RURG8060	UNITS
Peak Repetitive Reverse VoltageV _{RRM}	600	TVV
Working Peak Reverse Voltage	600	V
DC Blocking Voltage V _R	600	V
Average Rectified Forward Current $I_{F(AV)}$ ($T_C = 72^{\circ}C$)	80 CO	Α
Repetitive Peak Surge CurrentI _{FRM} (Square Wave, 20kHz)	160	Α
Nonrepetitive Peak Surge Current	800	Α
Maximum Power Dissipation	180	W
Avalanche Energy (See Figures 7 and 8)	50	mJ
Operating and Storage Temperature	-65 to 175	οС

Electrical Specifications $T_C = 25^{\circ}C$, Unless Otherwise Specified

SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNITS
V _F	I _F = 80A	OM.TW	N. A.	1.6	V. V
	$I_F = 80A, T_C = 150^{\circ}C$	OMITWO	- 11	1.4	OM-V
I _R	V _R = 600V	COM	- 1	250	μΑ
	$V_R = 600V, T_C = 150^{\circ}C$	COMITY	- W	2.0	mA
t _{rr}	$I_F = 1A$, $dI_F/dt = 100A/\mu s$	COMIT	_	75	ns
	$I_F = 80A$, $dI_F/dt = 100A/\mu s$	OM	_	85	ns
t _a	$I_F = 80A$, $dI_F/dt = 100A/\mu s$	OOY	40	WW.1	ns
t _b	$I_F = 80A$, $dI_F/dt = 100A/\mu s$	100 F. COL	25	-WW.	ns
$R_{ heta JC}$	W.100Y.COM.TW	N.1003.CO	William	0.83	°C/W

DEFINITIONS

 V_F = Instantaneous forward voltage (pw = 300 μ s, D = 2%).

I_R = Instantaneous reverse current.

t_{rr} = Reverse recovery time (See Figure 6), summation of t_a + t_b.

t_a = Time to reach peak reverse current (See Figure 6).

 t_b = Time from peak I_{RM} to projected zero crossing of I_{RM} based on a straight line from peak I_{RM} through 25% of I_{RM} (See Figure 6).

 $R_{\theta JC}$ = Thermal resistance junction to case

pw = pulse width.

D = duty cycle.

Typical Performance Curves

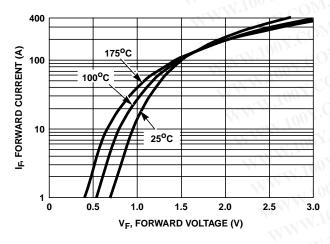


FIGURE 1. FORWARD CURRENT vs FORWARD VOLTAGE

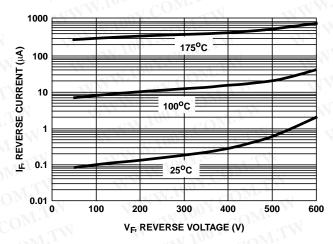


FIGURE 2. REVERSE CURRENT vs REVERSE VOLTAGE

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Typical Performance Curves (Continued)

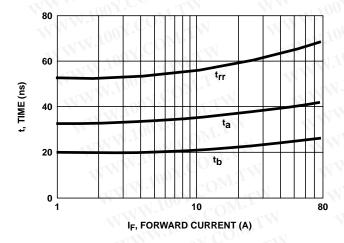


FIGURE 3. t_{rr}, t_a AND t_b CURVES vs FORWARD CURRENT

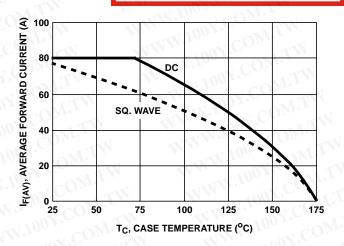


FIGURE 4. CURRENT DERATING CURVE

Test Circuits and Waveforms

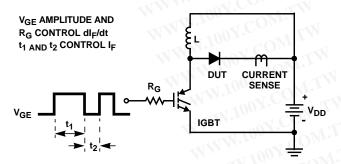


FIGURE 5. t_{rr} TEST CIRCUIT

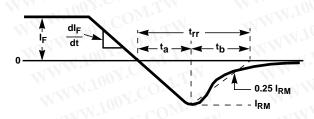


FIGURE 6. t_{rr} WAVEFORMS AND DEFINITIONS

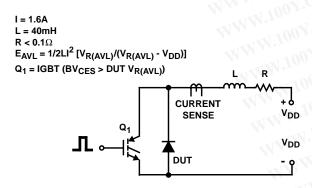


FIGURE 7. AVALANCHE ENERGY TEST CIRCUIT

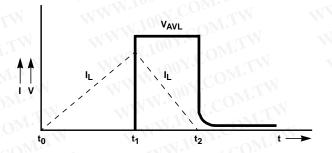


FIGURE 8. AVALANCHE CURRENT AND VOLTAGE WAVEFORMS

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